## NSN 5961-01-170-2170



Diode Semiconductor Device - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-170-2170 **Inclosure Material:** Metal **Overall Length:** 0.570 inches **Terminal Length:** 1.000 inches **Overall Diameter:** 0.235 inches **Function For Which Designed:** Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 171.0 breakdown voltage, dc and 189.0 breakdown voltage, dc **Current Rating Per Characteristic:** 200.00 amperes forward current, average preset and 34.00 amperes source cutoff current universal and 5.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 1500.0 watts small-signal output power, common-base pascal **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/500 government specification Shelf Life: N/a **Unit Of Measure:** 

Fiig: A110a0

No

**Demilitarization:**